TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

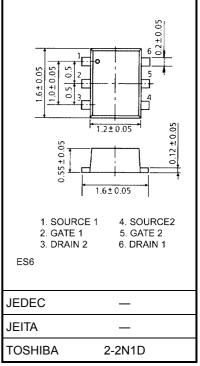
# SSM6N03FE

#### High Speed Switching Applications Analog Switch Applications

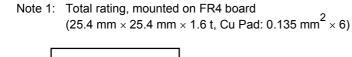
- Input impedance is high. Driving current is extremely low.
- Can be directly driven by a CMOS device even at low voltage due to low gate threshold voltage.
- High-speed switching.
- Housed in a ultra-small package which is suitable for high density mounting.

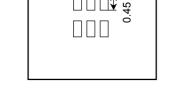
#### Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V <sub>DS</sub>	20	V
Gate-source voltage	V <sub>GSS</sub>	10	V
Drain current	۱ <sub>D</sub>	100	mA
Drain power dissipation	P <sub>D</sub> (Note 1)	150	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55~150	°C



Weight: g (typ.)

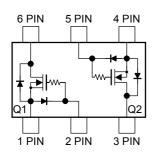




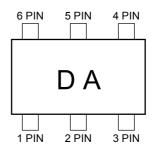
0.3 mm

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#### Equivalent Circuit (top view)



#### Marking



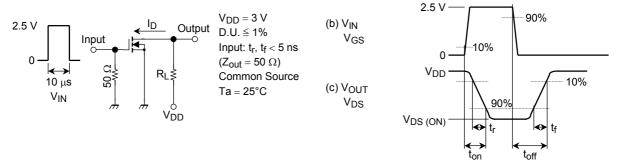
Unit: mm

#### Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = 10 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			1	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 100 \ \mu A, \ V_{GS} = 0 \ V$	20			V
Drain cut-off current		I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μA
Gate threshold voltage		V <sub>th</sub>	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 0.1 \text{ mA}$	0.7		1.3	V
Forward transfer admittance		Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}$	25	50		mS
Drain-source ON resistance		R <sub>DS (ON)</sub>	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$		4	12	Ω
Input capacitance		C <sub>iss</sub>	$V_{DS} = 3 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		11.0	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 3 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		3.3	_	pF
Output capacitance		C <sub>oss</sub>	$V_{DS} = 3 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		9.3	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 3 V, I_D = 10 mA, V_{GS} = 0~2.5 V$	_	0.16	_	μs
	Turn-off time	t <sub>off</sub>	$V_{DD} = 3 V, I_D = 10 mA, V_{GS} = 0~2.5 V$	_	0.19	_	

#### Switching Time Test Circuit

(a) Test circuit

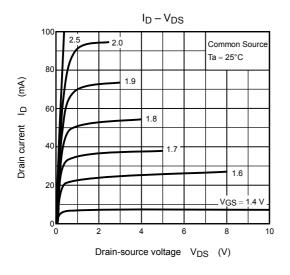


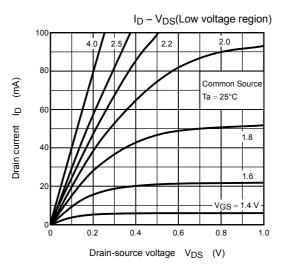
#### Precaution

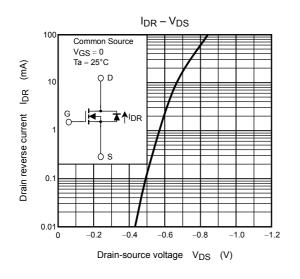
 $V_{th}$  can be expressed as voltage between gate and source when low operating current value is  $I_D = 100~\mu A$  for this product. For normal switching operation,  $V_{GS}$  (on) requires higher voltage than  $V_{th}$  and  $V_{GS}$  (off) requires lower voltage than  $V_{th}$ . (Relationship can be established as follows:  $V_{GS}$  (off) <  $V_{th}$  <  $V_{GS}$  (on) ) Please take this into consideration for using the device.  $V_{GS}$  recommended voltage of 2.5 V or higher to turn on this product.

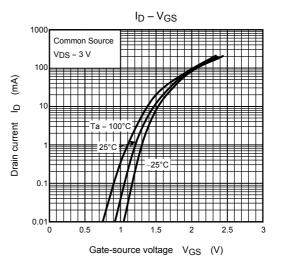
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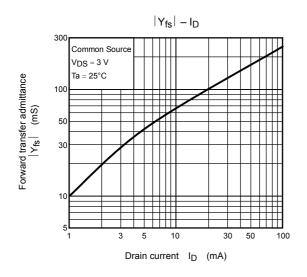
### (Q1, Q2 Common)

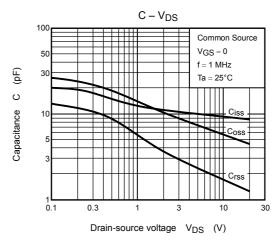






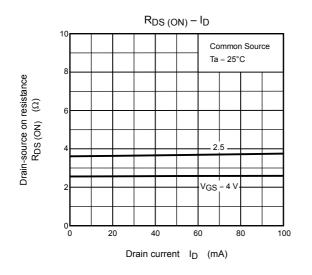


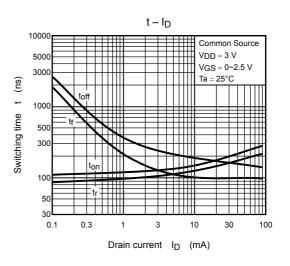


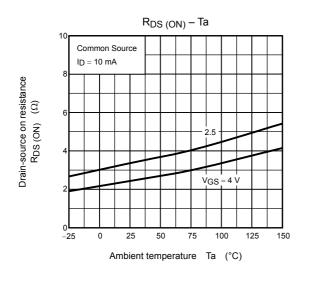


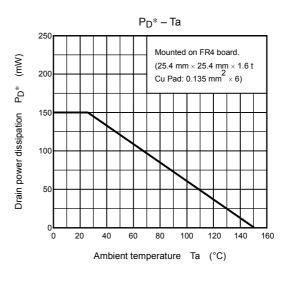
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### (Q1, Q2 Common)









\*: Total rating

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Handbook" etc.,

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